SD275SA45A/B/C

SENSITRON SEMICONDUCTOR

TECHNICAL DATA DATA SHEET 4111, REV A

SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop (150 °C T_J Operation)

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings (in SHD package):

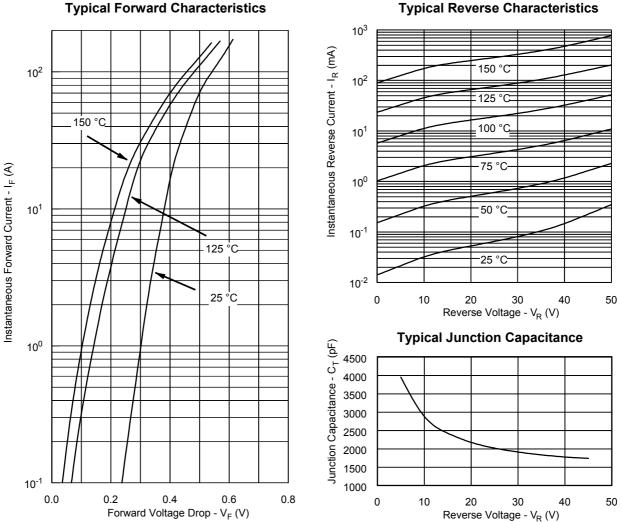
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	45	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	120	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	1650	A
Non-Repetitive Avalanche Energy	E_{AS}	T _J = 25 °C, I _{AS} = 11 A, L = 1.2 mH	76	mJ
Repetitive Avalanche Current I _{AR}		I_{AS} decay linearly to 0 in 1 µs f limited by $T_J max V_A=1.5V_R$	11	A
Max. Junction Temperature T _J		-	-65 to +150	°C
Max. Storage Temperature	T _{stg}	-	-65 to +150	°C

Electrical Characteristics⁽¹⁾:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 120A, Pulse, T _J = 25 °C	0.60	V
	V _{F2}	@ 120A, Pulse, T _J = 125 °C	0.57	V
Max. Reverse Current	I _{R1}	$@V_R = 45V$, Pulse,	9.0	mA
		T _J = 25 °C		
	I _{R2}	@V _R = 45V, Pulse,	420	mA
		T _J = 125 °C		
Max. Junction Capacitance	CT	@V _R = 5V, T _C = 25 °C	4800	pF
		$f_{SIG} = 1$ MHz, $V_{SIG} = 50$ mV (p-p)		

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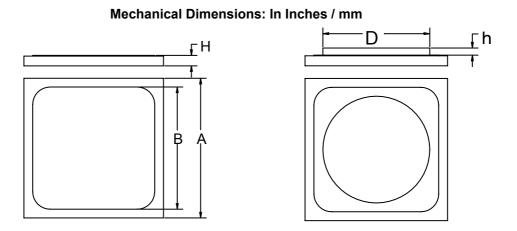


Typical Reverse Characteristics

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		Figure 2		
Α	В	D	Ъ	h
0.275±0.003	0.267±0.003	0.220±0.005	0.0155±0.001	0.011±0.002

Top side(Anode) metallization: A = A1 - 25 kÅ minimum, Figure 1 B = Ag - 30 kÅ minimum, Figure 1 C = Au - 12 kÅ min, Figure 2

Bottom side (Cathode) metallization: A, B, C = Ti/Ni/Ag - 30 kÅ minimum.

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